

-60V P-Channel Enhancement Mode MOSFET

Description

The XPX80P06TU uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 6V. This device is suitable for use as a Battery protection or in other Switching application.

Applications

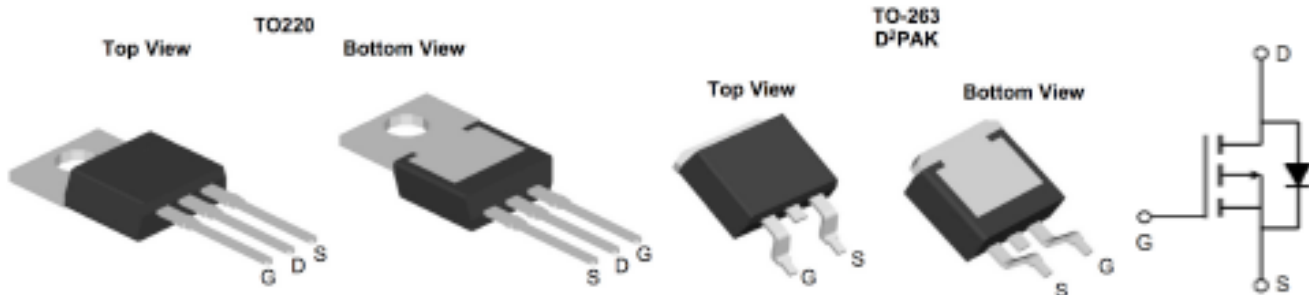
- Motor Drives
- Uninterruptible Power Supplies
- DC/DC converter
- General Purpose Applications



General Features

$V_{DS} = -60V$ $I_D = -82A$

$R_{DS(ON)} < 10m\Omega @ V_{GS} = -10V$



| Product ID | Pack | Marking | Qty(PCS) |
|------------|-----------|---------------------|----------|
| XPX80P06TU | TO-220-3L | XPX80P06TU XXX YYYY | 1000 |
| XPX80P06TU | TO-263-3L | XPX80P06TU XXX YYYY | 800 |

Absolute Maximum Ratings ($T_C = 25^\circ C$ unless otherwise noted)

| Symbol | Parameter | Rating | Units |
|---------------------------|--|------------|--------------|
| V_{DS} | Drain-Source Voltage | -60 | V |
| V_{GS} | Gate-Source Voltage | ± 20 | V |
| $I_D @ T_C = 25^\circ C$ | Continuous Drain Current, $-V_{GS} @ -10V^1$ | -82 | A |
| $I_D @ T_C = 100^\circ C$ | Continuous Drain Current, $-V_{GS} @ -10V^1$ | -52 | A |
| I_{DM} | Pulsed Drain Current ² | -328 | A |
| EAS | Single Pulse Avalanche Energy ³ | 450 | mJ |
| I_{AS} | Avalanche Current | 52 | A |
| $P_D @ T_C = 25^\circ C$ | Total Power Dissipation ⁴ | 110 | W |
| T_{STG} | Storage Temperature Range | -55 to 150 | $^\circ C$ |
| T_J | Operating Junction Temperature Range | -55 to 150 | $^\circ C$ |
| $R_{\theta JA}$ | Thermal Resistance Junction-Ambient ¹ | 0.70 | $^\circ C/W$ |
| $R_{\theta JC}$ | Thermal Resistance Junction-Case ¹ | 60 | $^\circ C/W$ |

Electrical Characteristics (T_c=25°C unless otherwise noted)

| Symbol | Parameter | Conditions | Min. | Typ. | Max. | Unit |
|------------------------|--|--|------|--------|------|-------|
| BVDSS | Drain-Source Breakdown Voltage | V _{GS} =0V, I _D =-250uA | -60 | -68 | --- | V |
| ΔBVDSS/ΔT _J | BV _{DSS} Temperature Coefficient | Reference to 25°C, I _D =-1mA | --- | -0.035 | --- | V/°C |
| RDS(ON) | Static Drain-Source On-Resistance ² | V _{GS} =-10V, I _D =-20A | --- | 10 | 12 | mΩ |
| | | V _{GS} =-4.5V, I _D =-15A | --- | 13 | 16 | |
| VGS(th) | Gate Threshold Voltage | V _{GS} =V _{DS} , I _D =-250uA | -1.0 | -2.1 | -3.0 | V |
| ΔVGS(th) | VGS(th) Temperature Coefficient | | --- | 4.28 | --- | mV/°C |
| IDSS | Drain-Source Leakage Current | V _{DS} =-60V, V _{GS} =0V, T _J =25°C | --- | --- | 1 | uA |
| | | V _{DS} =-60V, V _{GS} =0V, T _J =55°C | --- | --- | 5 | |
| IGSS | Gate-Source Leakage Current | V _{GS} =±20V, V _{DS} =0V | --- | --- | ±100 | nA |
| gfs | Forward Transconductance | V _{DS} =-5V, I _D =-20A | --- | 50 | --- | S |
| R _g | Gate Resistance | V _{DS} =0V, V _{GS} =0V, f=1MHz | --- | 2.0 | --- | Ω |
| Q _g | Total Gate Charge (-4.5V) | V _{DS} =-30V, V _{GS} =-10V, I _D =-20A | --- | 56 | --- | nC |
| Q _{gs} | Gate-Source Charge | | --- | 11 | --- | |
| Q _{gd} | Gate-Drain Charge | | --- | 9 | --- | |
| Td(on) | Turn-On Delay Time | V _{DD} =-30V, V _{GS} =-10V, R _G =3Ω, I _D =-20A | --- | 4.5 | --- | ns |
| T _r | Rise Time | | --- | 2.5 | --- | |
| Td(off) | Turn-Off Delay Time | | --- | 14.5 | --- | |
| T _f | Fall Time | | --- | 3.8 | --- | |
| C _{iss} | Input Capacitance | V _{DS} =-15V, V _{GS} =0V, f=1MHz | --- | 3500 | --- | pF |
| C _{oss} | Output Capacitance | | --- | 600 | --- | |
| Crss | Reverse Transfer Capacitance | | --- | 25 | --- | |
| I _s | Continuous Source Current ^{1,5} | V _G =V _D =0V, Force Current | --- | --- | -80 | A |
| ISM | Pulsed Source Current ^{2,5} | | --- | --- | -240 | A |
| VSD | Diode Forward Voltage ² | V _{GS} =0V, I _S =-1A, T _J =25°C | --- | --- | -1.2 | V |

Note :

- 1、 The data tested by surface mounted on a 1 inch 2 FR-4 board with 20Z copper.
- 2、 The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3、 The EAS data shows Max. rating . The test condition is V_{DD} =-48V, V_{GS} =-10V, L=0.1mH, I_{AS} =-52A
- 4、 The power dissipation is limited by 150°C junction temperature
- 5、 The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

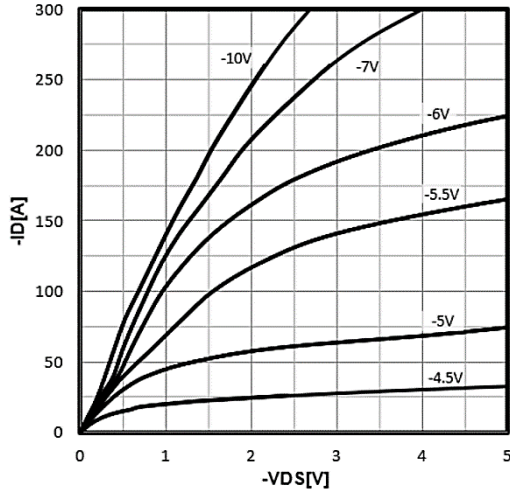


Figure 1. Type. Output Characteristics (Tj=25 °C)

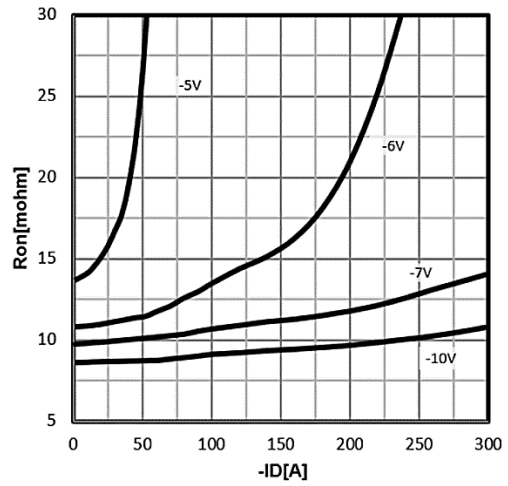


Figure 2. Type. drain-source on resistance

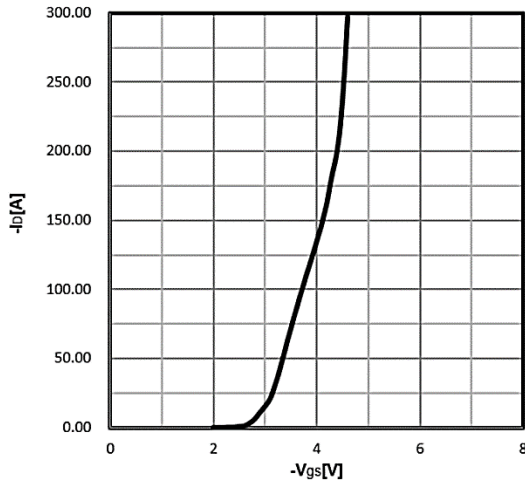


Figure 3. Type. transfer characteristics

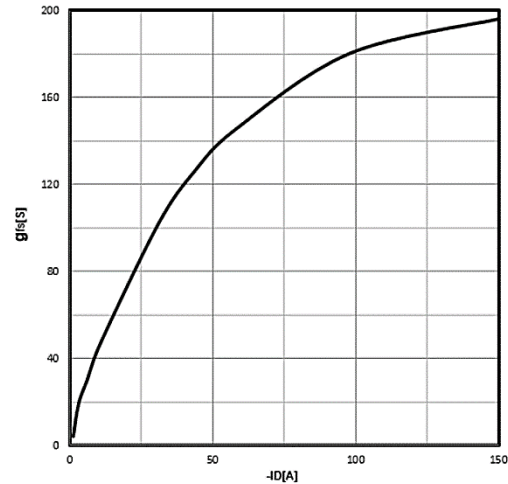


Figure 4. Type. forward transconductance

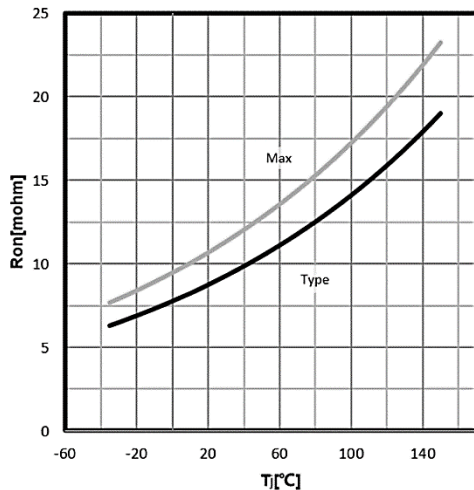


Figure 5. Drain-source on-state resistance
RDS(on) = f(Tj); ID = 80A; VGS = 10V

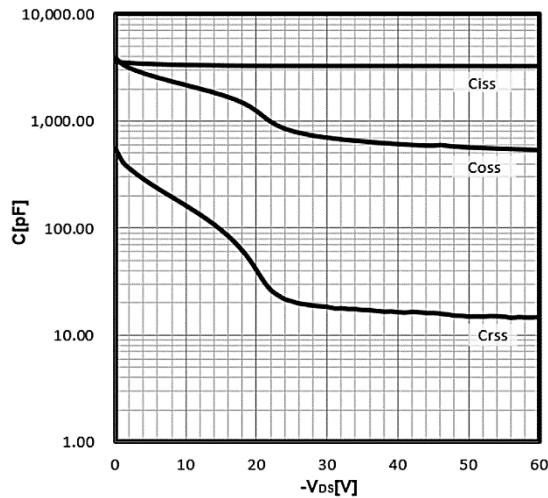


Figure 6. Body-Diode Characteristics
C=f(VDS); VGS = 0V; f=1MHz

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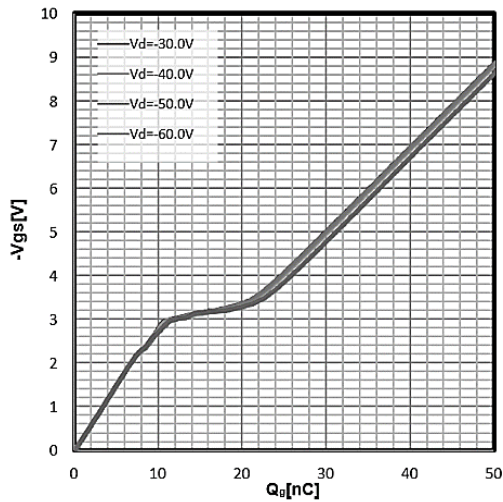


Figure 7. Typ. gate charge
 $V_{GS} = f(Q_{gate})$; $I_D = 20A$

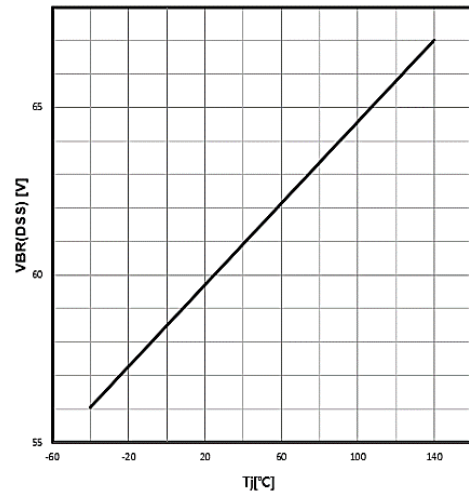


Figure 8. Drain Current Derating
 $V_{BR(DSS)} = f(T_j)$; $I_D = 250\mu A$

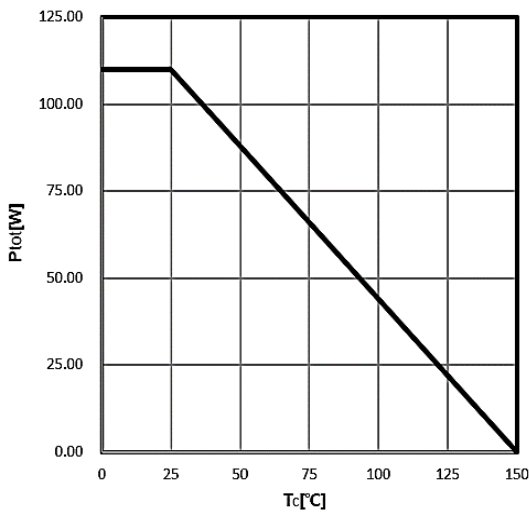


Figure 7. Power Dissipation

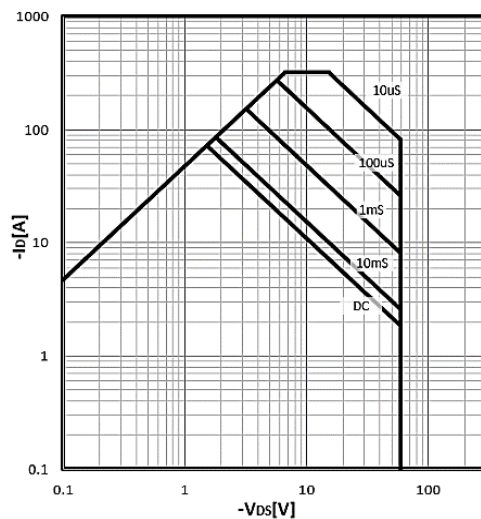


Figure 8. Safe operating area

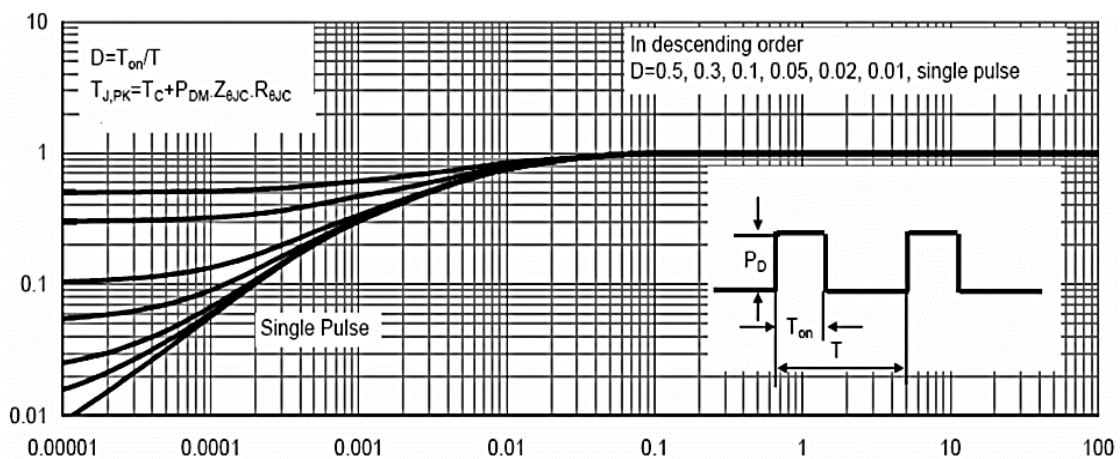
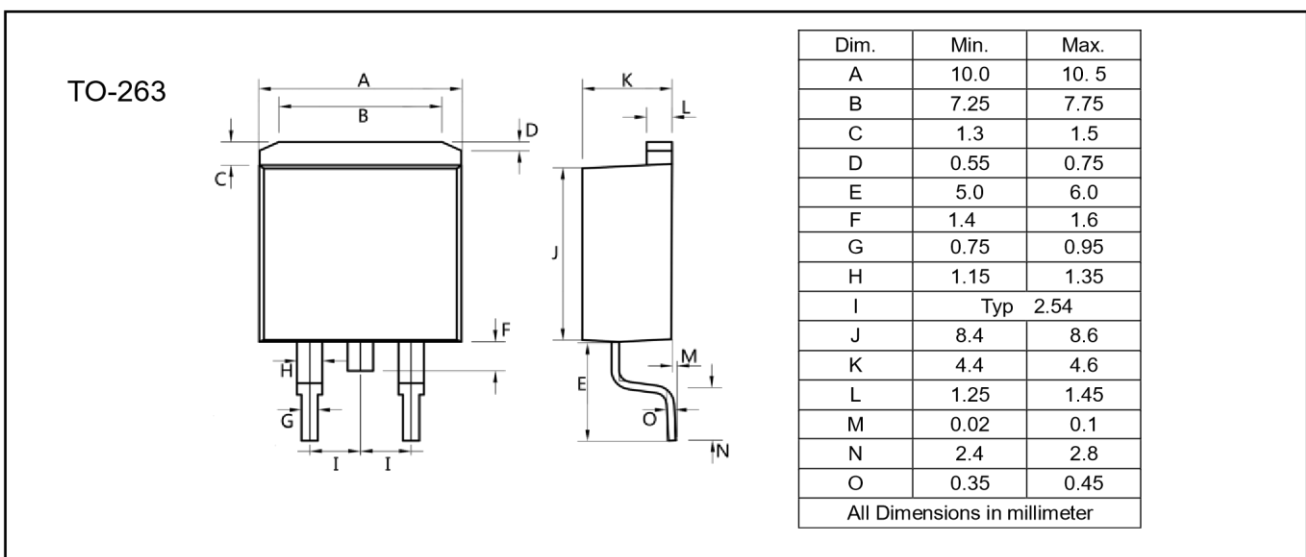
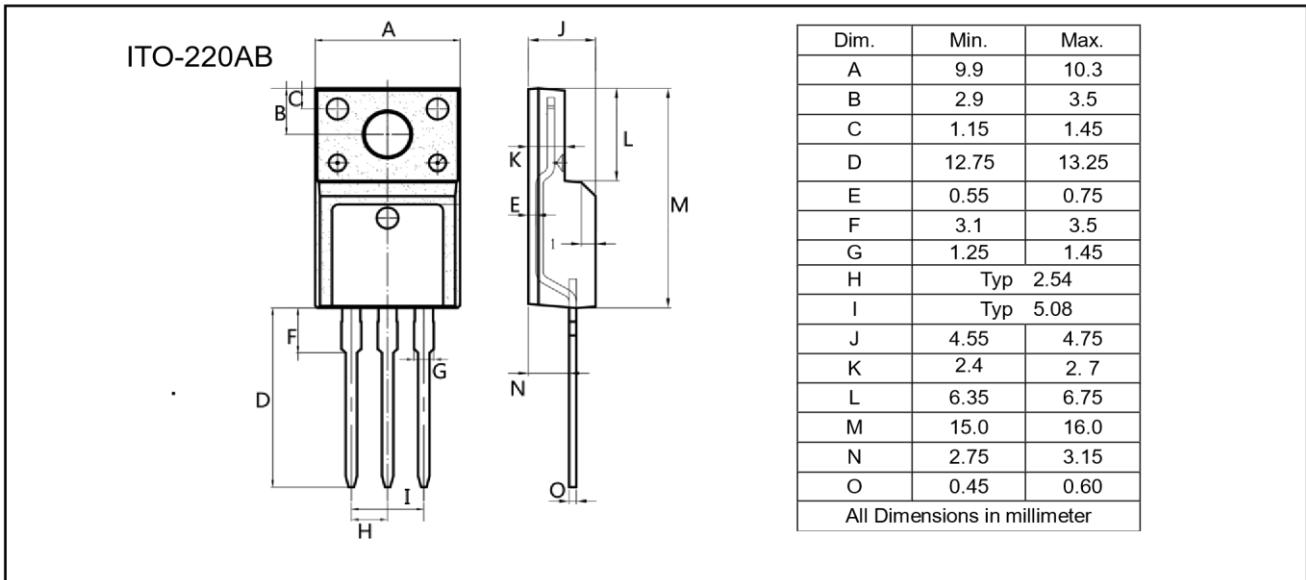
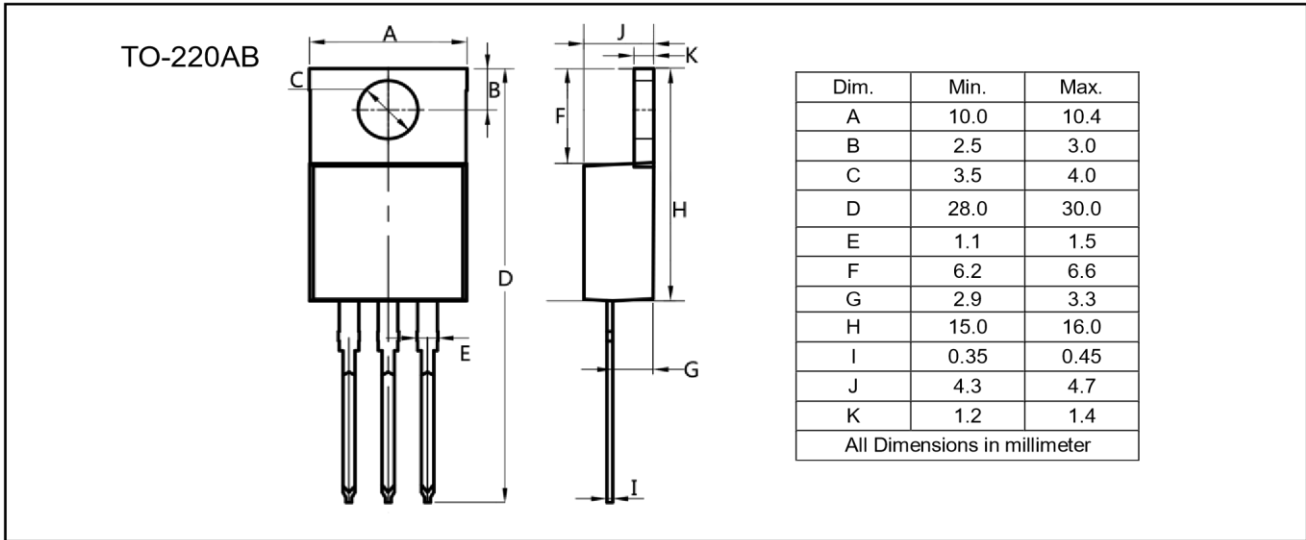


Figure 10. Max. transient thermal impedance

$Z_{thJC} = f(t_p)$

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Flow (wave) soldering (solder dipping)

| Product | Peak Temperature | Dipping Time |
|----------------|------------------|--------------|
| Pb device | 245°C ±5°C | 5sec ±1sec |
| Pb-Free device | 260°C +0/-5°C | 5sec ±1sec |



This integrated circuit can be damaged by ESD. UniverChip Corporation recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedure can cause damage. ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

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